2SC5725

Silicon NPN epitaxial planar type

For DC-DC converter

Features

• Low collector-emitter saturation voltage V_{CE(sat)}

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter

Collector-base voltage (Emitter open)

Collector-emitter voltage (Base open)

Emitter-base voltage (Collector open)

Collector current

Peak collector current

Junction temperature

Storage temperature

Collector power dissipation *

• Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

Symbol

V_{CBO}

VCEO

V_{EBO}

IC

I_{CP}

 P_C

Ti

T_{stg}

Rating

20

15

5

2

6

600

150

-55 to +150

Unit

V

V

V

А

Α

mW °C

°C

Unit: mm 0.40+0.10 0.16+0.10 Ц3 -1 20 20 ÷ 2 **1**1 (0.95) (0.95) (0.65) 1.9±0.1 2.90+0.20 1.1+0.2 1.1_0.3 1: Base 0 to 0.1 2: Emitter 3: Collector EIAJ: SC-59 Mini3-G1 Package

Marking Symbol: 3C

Note) *: Measure on the ceramic substrate at 15 mm × 15 mm × 0.6 mm

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$	20	ş		V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$	15			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = 10 \ \mu A, I_{\rm C} = 0$	-5			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 10 \text{ V}, I_E = 0$,		0.1	μΑ
Forward current transfer ratio *	h _{FE1}	$V_{CE} = 2 V, I_C = 100 mA$	200		800	
	h _{FE2}	$V_{CE} = 2 V, I_C = 1.5 A$	120			
Collector-emitter saturation voltage *	V _{CE(sat)}	$I_{\rm C} = 0.5 \text{ A}, I_{\rm B} = 25 \text{ mA}$		40	100	mV
		$I_{\rm C} = 1.5 \text{ A}, I_{\rm B} = 30 \text{ mA}$		130	280	
Transition frequency	f _T	$V_{CB} = 10 \text{ V}, \text{ I}_{\text{E}} = -50 \text{ mA}, \text{ f} = 200 \text{ MHz}$		280		MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		15	25	pF
(Common base, input open circuited)						

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Pulse measurement

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